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October 2013

# **FDP2710**

# N-Channel PowerTrench® MOSFET 250 V, 50 A, 42.5 m $\Omega$

### **Features**

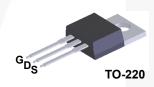
- $R_{DS(on)}$  = 36.3 m $\Omega$  ( Typ.)@  $V_{GS}$  = 10 V,  $I_D$  = 25 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench technology for Extremely Low  $R_{\text{DS(on)}}$
- · High Power and Current Handing Capability
- · RoHS Compliant

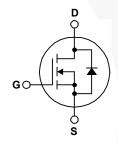
## **General Description**

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench<sup>®</sup> process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

# **Applications**

- · Consumer Appliances
- · Synchronous Rectification





## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol		Parameter		FDP2710	Unit
V <sub>DS</sub>	Drain-Source Voltage			250	V
V <sub>GS</sub>	Gate-Source voltage			± 30	V
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25 - Continuous (T <sub>C</sub> = 10	,	50 31.3	A A
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	See Figure 9	A
E <sub>AS</sub>	Single Pulsed Ava	lanche Energy	(Note 2)	145	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C			260 2.1	W W/°C
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		urpose,	300	°C

## **Thermal Characteristics**

Symbol	Parameter	FDP2710	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.48	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

# **Package Marking and Ordering Information**

<b>Device Marking</b>	Device	Package	Reel Size	Tape Width	Quantity
FDP2710	FDP2710	TO-220	Tube	N/A	50 units

# **Electrical Characteristics** T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
Off Charac	Off Characteristics							
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_D = 250\mu A$ , $T_J = 25^{\circ}C$	250			V		
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C		0.25		V/°C		
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 250V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 250V, V <sub>GS</sub> = 0V, T <sub>C</sub> = 125°C			10 500	μA μA		
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30V, V <sub>DS</sub> = 0V			100	nA		
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30V, V <sub>DS</sub> = 0V			-100	nA		
On Charac	teristics				_			
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0	4.0	5.0	V		
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 25A		36.3	42.5	mΩ		
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10V, I <sub>D</sub> = 25A		63		S		
Dynamic C	Dynamic Characteristics							
C <sub>iss</sub>	Input Capacitance		\	5470	7280	pF		
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz		426	570	pF		
C <sub>rss</sub>	Reverse Transfer Capacitance	- 1 = 1.UIVIMZ		97	146	pF		
Switching	Characteristics							
t <sub>d(on)</sub>	Turn-On Delay Time			80	170	ns		
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 125V, I_D = 50A$ $V_{GS} = 10V, R_{GEN} = 25\Omega$		252	515	ns		
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GS</sub> = 10V, N <sub>GEN</sub> = 2352		112	235	ns		
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		154	320	ns		
Qg	Total Gate Charge			78	101	nC		
Q <sub>gs</sub>	Gate-Source Charge	$V_{DS} = 125V, I_D = 50A$ $V_{GS} = 10V$	-	34		nC		
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)	/	18		nC		
Drain-Sour	rce Diode Characteristics and Maximun	n Ratings		l		ı		
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				50	Α		
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Fo	orward Current			150	Α		
$V_{SD}$	Drain-Source Diode Forward Voltage	Source Diode Forward Voltage V <sub>GS</sub> = 0V, I <sub>S</sub> = 50A			1.2	V		
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0V, I <sub>S</sub> = 50A		163		ns		
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> /dt =100A/μs		1.3	/	μС		

#### Notes:

<sup>1.</sup> Repetitive Rating: Pulse width limited by maximum junction temperature

<sup>2.</sup> L = 1mH, I<sub>AS</sub> = 17A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 $\Omega$ , Starting T<sub>J</sub> = 25 $^{\circ}$ C

<sup>3.</sup> I  $_{SD} \le 50 \text{A}, \text{ di/dt} \le 100 \text{A/}\mu\text{s}, \text{ V}_{DD} \le \text{BV}_{DSS}, \text{ Starting T}_J = 25^{\circ}\text{C}$ 

<sup>4.</sup> Essentially Independent of Operating Temperature Typical Characteristics

# **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

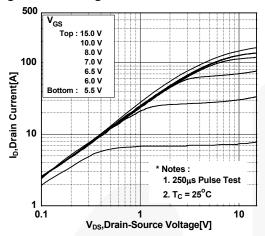


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

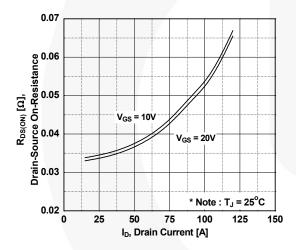


Figure 5. Capacitance Characteristics

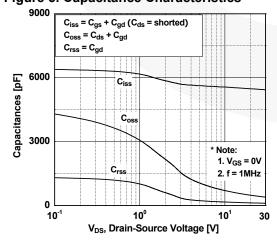


Figure 2. Transfer Characteristics

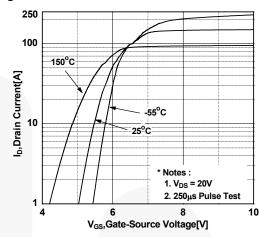
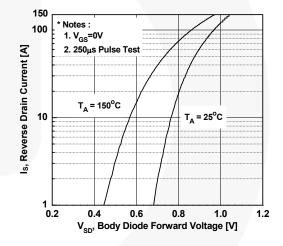
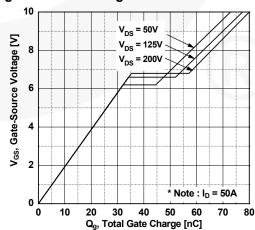


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue



**Figure 6. Gate Charge Characteristics** 



# **Typical Performance Characteristics (Continued)**

Figure 7. Breakdown Voltage Variation vs. Temperature

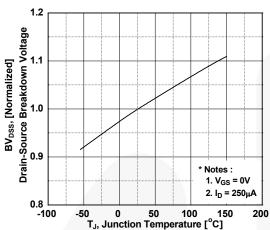


Figure 9. Maximum Safe Operating Area

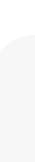


Figure 8. On-Resistance Variation vs. Temperature

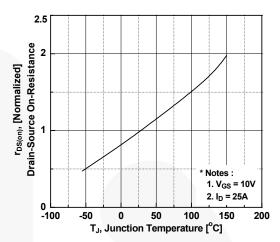
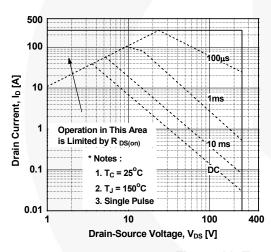


Figure 10. Maximum Drain Current vs. Case Temperature



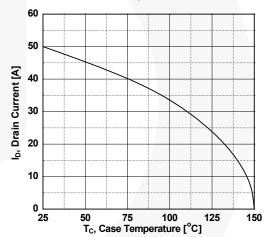


Figure 11. Transient Thermal Response Curve

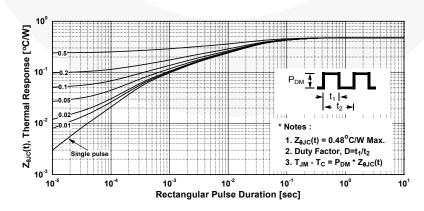


Figure 12. Gate Charge Test Circuit & Waveform

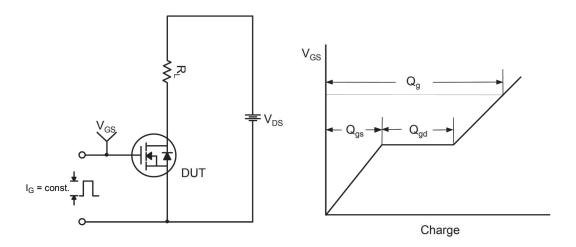


Figure 13. Resistive Switching Test Circuit & Waveforms

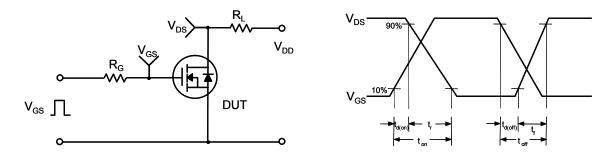
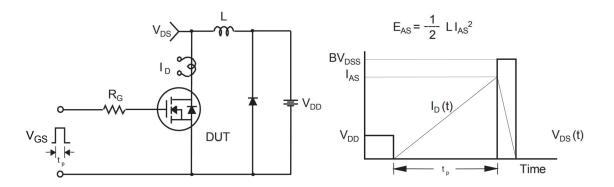


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



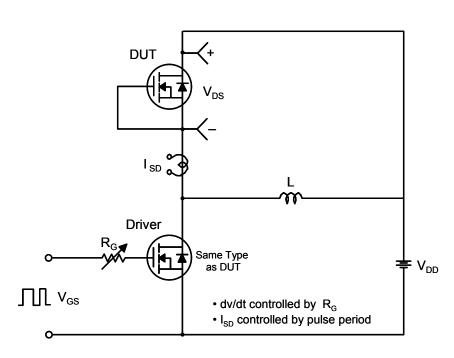
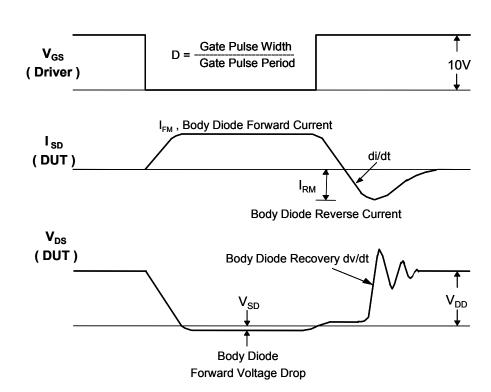


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



## **Mechanical Dimensions**

# TO-220 3L

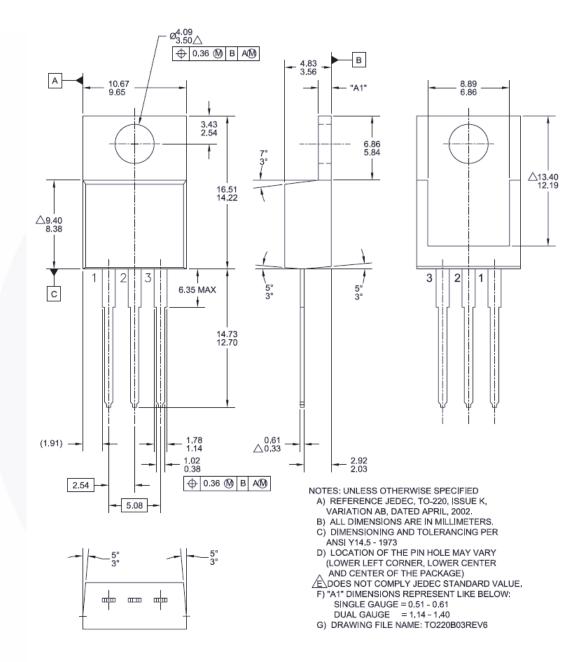


Figure 16. TO-220, Molded, 3Lead, Jedec Variation AB

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Dimension in Millimeters





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